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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	276480
Number of I/O	252
Number of Gates	1500000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	676-BGA
Supplier Device Package	676-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/afs1500-fg676

VersaNet Timing Characteristics

Global clock delays include the central rib delay, the spine delay, and the row delay. Delays do not include I/O input buffer clock delays, as these are dependent upon I/O standard, and the clock may be driven and conditioned internally by the CCC module. [Table 2-5](#), [Table 2-6](#), [Table 2-7](#), and [Table 2-8](#) on [page 2-17](#) present minimum and maximum global clock delays within the device. Minimum and maximum delays are measured with minimum and maximum loading, respectively.

Timing Characteristics

Table 2-5 • AFS1500 Global Resource Timing
Commercial Temperature Range Conditions: $T_j = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.53	1.75	1.74	1.99	2.05	2.34	ns
t_{RCKH}	Input High Delay for Global Clock	1.53	1.79	1.75	2.04	2.05	2.40	ns
t_{RCKMPWH}	Minimum Pulse Width High for Global Clock							ns
t_{RCKMPWL}	Minimum Pulse Width Low for Global Clock							ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7](#) on [page 3-9](#).

Table 2-6 • AFS600 Global Resource Timing
Commercial Temperature Range Conditions: $T_j = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	1.27	1.49	1.44	1.70	1.69	2.00	ns
t_{RCKH}	Input High Delay for Global Clock	1.26	1.54	1.44	1.75	1.69	2.06	ns
t_{RCKMPWH}	Minimum Pulse Width High for Global Clock							ns
t_{RCKMPWL}	Minimum Pulse Width Low for Global Clock							ns
t_{RCKSW}	Maximum Skew for Global Clock		0.27		0.31		0.36	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7](#) on [page 3-9](#).

Clock Conditioning Circuits

In Fusion devices, the CCCs are used to implement frequency division, frequency multiplication, phase shifting, and delay operations.

The CCCs are available in six chip locations—each of the four chip corners and the middle of the east and west chip sides.

Each CCC can implement up to three independent global buffers (with or without programmable delay), or a PLL function (programmable frequency division/multiplication, phase shift, and delays) with up to three global outputs. Unused global outputs of a PLL can be used to implement independent global buffers, up to a maximum of three global outputs for a given CCC.

A global buffer can be placed in any of the three global locations (CLKA-GLA, CLKB-GLB, and CLKC-GLC) of a given CCC.

A PLL macro uses the CLKA CCC input to drive its reference clock. It uses the GLA and, optionally, the GLB and GLC global outputs to drive the global networks. A PLL macro can also drive the YB and YC regular core outputs. The GLB (or GLC) global output cannot be reused if the YB (or YC) output is used (Figure 2-19). Refer to the "PLL Macro" section on page 2-27 for more information.

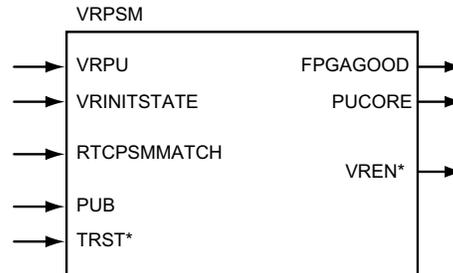
Each global buffer, as well as the PLL reference clock, can be driven from one of the following:

- 3 dedicated single-ended I/Os using a hardwired connection
- 2 dedicated differential I/Os using a hardwired connection
- The FPGA core

The CCC block is fully configurable, either via flash configuration bits set in the programming bitstream or through an asynchronous interface. This asynchronous interface is dynamically accessible from inside the Fusion device to permit changes of parameters (such as divide ratios) during device operation. To increase the versatility and flexibility of the clock conditioning system, the CCC configuration is determined either by the user during the design process, with configuration data being stored in flash memory as part of the device programming procedure, or by writing data into a dedicated shift register during normal device operation. This latter mode allows the user to dynamically reconfigure the CCC without the need for core programming. The shift register is accessed through a simple serial interface. Refer to the "UJTAG Applications in Microsemi's Low-Power Flash Devices" chapter of the *Fusion FPGA Fabric User Guide* and the "CCC and PLL Characteristics" section on page 2-28 for more information.

Voltage Regulator and Power System Monitor (VRPSM)

The VRPSM macro controls the power-up state of the FPGA. The power-up bar (PUB) pin can turn on the voltage regulator when set to 0. TRST can enable the voltage regulator when deasserted, allowing the FPGA to power-up when user want access to JTAG ports. The inputs VRINITSTATE and RTCPSMMATCH come from the flash bits and RTC, and can also power up the FPGA.



Note: *Signals are hardwired internally and do not exist in the macro core.

Figure 2-30 • VRPSM Macro

Table 2-17 • VRPSM Signal Descriptions

Signal Name	Width	Direction	Function
VRPU	1	In	Voltage Regulator Power-Up 0 – Voltage regulator disabled. PUB must be floated or pulled up, and the TRST pin must be grounded to disable the voltage regulator. 1 – Voltage regulator enabled
VRINITSTATE	1	In	Voltage Regulator Initial State Defines the voltage Regulator status upon power-up of the 3.3 V. The signal is configured by Libero SoC when the VRPSM macro is generated. Tie off to 1 – Voltage regulator enables when 3.3 V is powered. Tie off to 0 – Voltage regulator disables when 3.3 V is powered.
RTCPSMMATCH	1	In	RTC Power System Management Match Connect from RTCPSMATCH signal from RTC in AB 0 transition to 1 turns on the voltage regulator
PUB	1	In	External pin, built-in weak pull-up Power-Up Bar 0 – Enables voltage regulator at all times
TRST*	1	In	External pin, JTAG Test Reset 1 – Enables voltage regulator at all times
FPGAGOOD	1	Out	Indicator that the FPGA is powered and functional No need to connect if it is not used. 1 – Indicates that the FPGA is powered up and functional. 0 – Not possible to read by FPGA since it has already powered off.
PUCORE	1	Out	Power-Up Core Inverted signal of PUB. No need to connect if it is not used.
VREN*	1	Out	Voltage Regulator Enable Connected to 1.5 V voltage regulator in Fusion device internally. 0 – Voltage regulator disables 1 – Voltage regulator enables

Note: *Signals are hardwired internally and do not exist in the macro core.

Modes of Operation

There are two read modes and one write mode:

- Read Nonpipelined (synchronous—1 clock edge): In the standard read mode, new data is driven onto the RD bus in the same clock cycle following RA and REN valid. The read address is registered on the read port clock active edge, and data appears at RD after the RAM access time. Setting PIPE to OFF enables this mode.
- Read Pipelined (synchronous—2 clock edges): The pipelined mode incurs an additional clock delay from the address to the data but enables operation at a much higher frequency. The read address is registered on the read port active clock edge, and the read data is registered and appears at RD after the second read clock edge. Setting PIPE to ON enables this mode.
- Write (synchronous—1 clock edge): On the write clock active edge, the write data is written into the SRAM at the write address when WEN is High. The setup times of the write address, write enables, and write data are minimal with respect to the write clock. Write and read transfers are described with timing requirements in the "SRAM Characteristics" section on page 2-63 and the "FIFO Characteristics" section on page 2-72.

RAM Initialization

Each SRAM block can be individually initialized on power-up by means of the JTAG port using the UJTAG mechanism (refer to the "JTAG IEEE 1532" section on page 2-229 and the *Fusion SRAM/FIFO Blocks* application note). The shift register for a target block can be selected and loaded with the proper bit configuration to enable serial loading. The 4,608 bits of data can be loaded in a single operation.

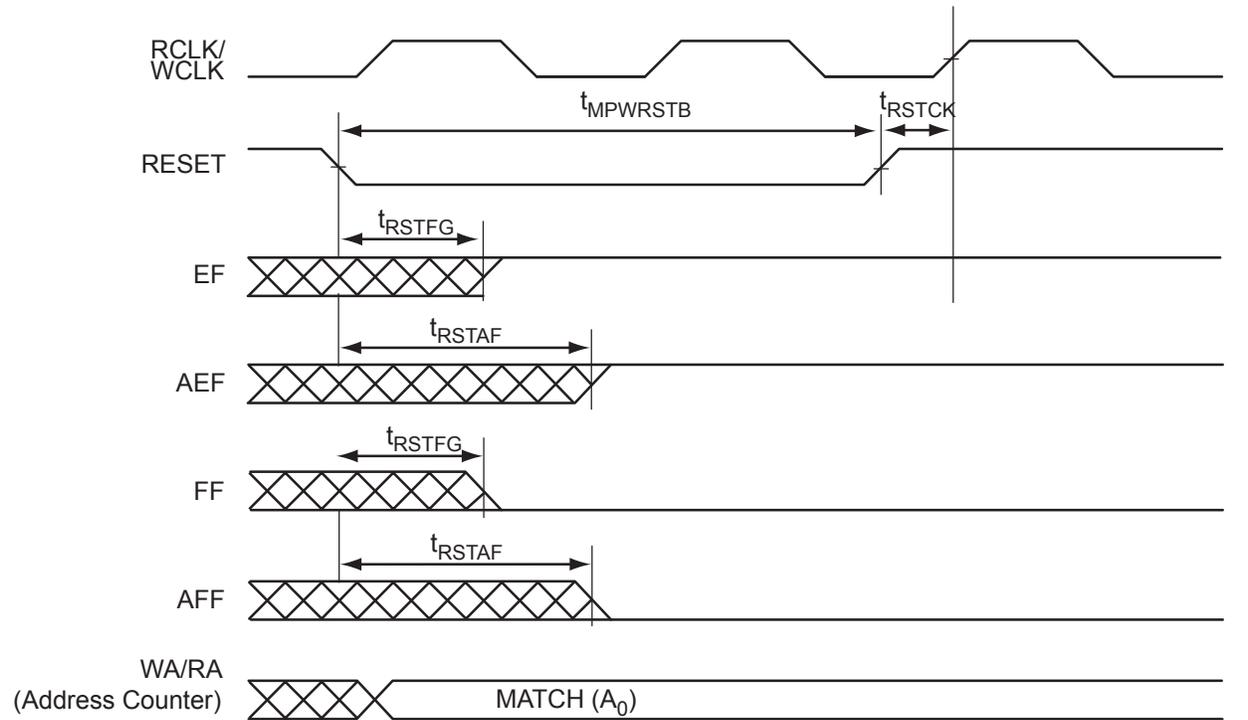


Figure 2-59 • FIFO Reset

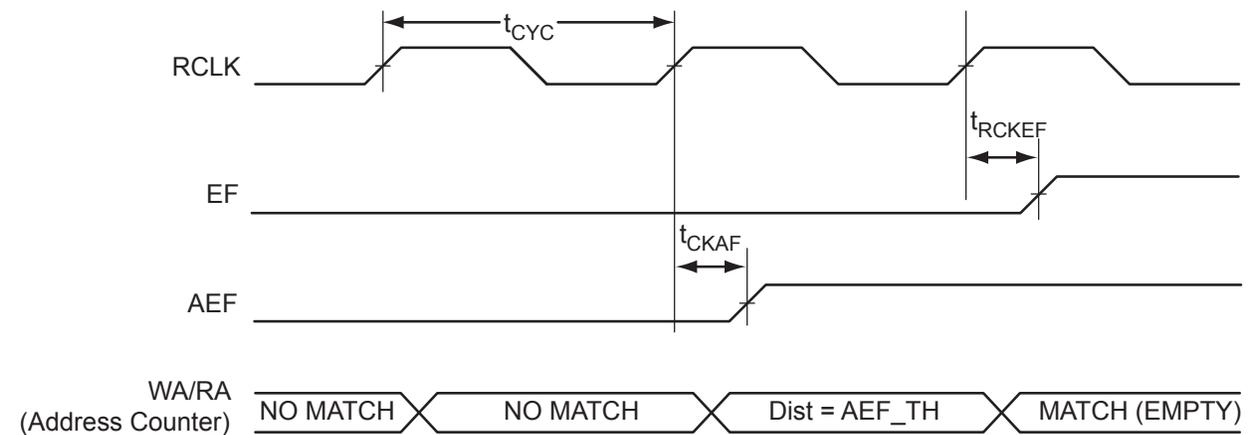


Figure 2-60 • FIFO EMPTY Flag and AEMPTY Flag Assertion

Gain Error

The gain error of an ADC indicates how well the slope of an actual transfer function matches the slope of the ideal transfer function. Gain error is usually expressed in LSB or as a percent of full-scale (%FSR). Gain error is the full-scale error minus the offset error (Figure 2-84).

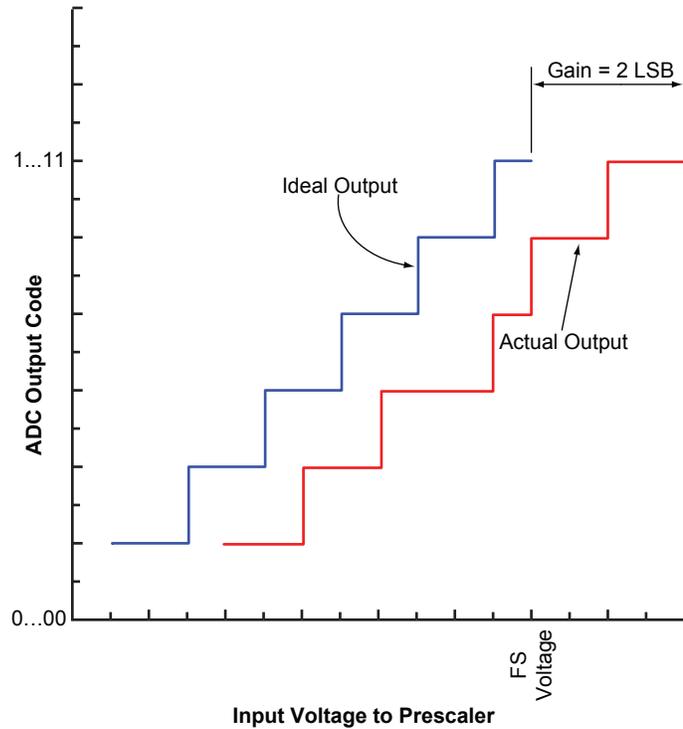


Figure 2-84 • Gain Error

Gain Error Drift

Gain-error drift is the variation in gain error due to a change in ambient temperature, typically expressed in ppm/°C.

INL – Integral Non-Linearity

INL is the deviation of an actual transfer function from a straight line. After nullifying offset and gain errors, the straight line is either a best-fit straight line or a line drawn between the end points of the transfer function (Figure 2-85).

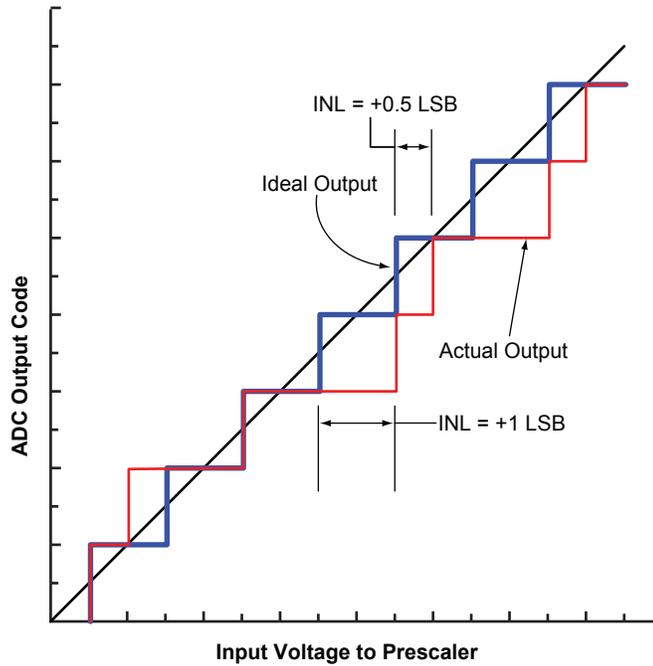


Figure 2-85 • Integral Non-Linearity (INL)

LSB – Least Significant Bit

In a binary number, the LSB is the least weighted bit in the group. Typically, the LSB is the furthest right bit. For an ADC, the weight of an LSB equals the full-scale voltage range of the converter divided by 2^N , where N is the converter’s resolution.

EQ 13 shows the calculation for a 10-bit ADC with a unipolar full-scale voltage of 2.56 V:

$$1 \text{ LSB} = (2.56 \text{ V} / 2^{10}) = 2.5 \text{ mV}$$

EQ 13

No Missing Codes

An ADC has no missing codes if it produces all possible digital codes in response to a ramp signal applied to the analog input.

Similarly,
 Min. Output Voltage = (Max. Negative input offset) + (Input Voltage x Max. Negative Channel Gain)
 = (-88 mV) + (5 V x 0.96) = **4.712 V**

Calculating Accuracy for a Calibrated Analog Channel

Formula

For a given prescaler range, EQ 31 gives the output voltage.

$$\text{Output Voltage} = \text{Channel Error in V} + \text{Input Voltage}$$

EQ 31

where

$$\text{Channel Error in V} = \text{Total Channel Error in LSBs} \times \text{Equivalent voltage per LSB}$$

Example

Input Voltage = 5 V
 Chosen Prescaler range = 8 V range
 Refer to [Table 2-52 on page 2-123](#).

Max. Output Voltage = Max. Positive Channel Error in V + Input Voltage
 Max. Positive Channel Error in V = (6 LSB) x (8 mV per LSB in 10-bit mode) = 48 mV
 Max. Output Voltage = 48 mV + 5 V = **5.048 V**

Similarly,
 Min. Output Voltage = Max. Negative Channel Error in V + Input Voltage = (-48 mV) + 5 V = **4.952 V**

Calculating LSBs from a Given Error Budget

Formula

For a given prescaler range,

$$\text{LSB count} = \pm (\text{Input Voltage} \times \text{Required \% error}) / (\text{Equivalent voltage per LSB})$$

Example

Input Voltage = 3.3 V
 Required error margin = 1%
 Refer to [Table 2-52 on page 2-123](#).
 Equivalent voltage per LSB = 16 mV for a 16V prescaler, with ADC in 10-bit mode
 LSB Count = $\pm (5.0 \text{ V} \times 1\%) / (0.016)$
 LSB Count = **± 3.125**
 Equivalent voltage per LSB = **8 mV** for an 8 V prescaler, with ADC in 10-bit mode
 LSB Count = $\pm (5.0 \text{ V} \times 1\%) / (0.008)$
 LSB Count = **± 6.25**

The 8 V prescaler satisfies the calculated LSB count accuracy requirement (see [Table 2-52 on page 2-123](#)).

Analog Quad ACM Description

Table 2-56 maps out the ACM space associated with configuration of the Analog Quads within the Analog Block. Table 2-56 shows the byte assignment within each quad and the function of each bit within each byte. Subsequent tables will explain each bit setting and how it corresponds to a particular configuration. After 3.3 V and 1.5 V are applied to Fusion, Analog Quad configuration registers are loaded with default settings until the initialization and configuration state machine changes them to user-defined settings.

Table 2-56 • Analog Quad ACM Byte Assignment

Byte	Bit	Signal (Bx)	Function	Default Setting
Byte 0 (AV)	0	B0[0]	Scaling factor control – prescaler	Highest voltage range
	1	B0[1]		
	2	B0[2]		
	3	B0[3]	Analog MUX select	Prescaler
	4	B0[4]	Current monitor switch	Off
	5	B0[5]	Direct analog input switch	Off
	6	B0[6]	Selects V-pad polarity	Positive
	7	B0[7]	Prescaler op amp mode	Power-down
Byte 1 (AC)	0	B1[0]	Scaling factor control – prescaler	Highest voltage range
	1	B1[1]		
	2	B1[2]		
	3	B1[3]	Analog MUX select	Prescaler
	4	B1[4]		
	5	B1[5]	Direct analog input switch	Off
	6	B1[6]	Selects C-pad polarity	Positive
	7	B1[7]	Prescaler op amp mode	Power-down
Byte 2 (AG)	0	B2[0]	Internal chip temperature monitor *	Off
	1	B2[1]	Spare	–
	2	B2[2]	Current drive control	Lowest current
	3	B2[3]		
	4	B2[4]	Spare	–
	5	B2[5]	Spare	–
	6	B2[6]	Selects G-pad polarity	Positive
	7	B2[7]	Selects low/high drive	Low drive
Byte 3 (AT)	0	B3[0]	Scaling factor control – prescaler	Highest voltage range
	1	B3[1]		
	2	B3[2]		
	3	B3[3]	Analog MUX select	Prescaler
	4	B3[4]		
	5	B3[5]	Direct analog input switch	Off
	6	B3[6]	–	–
	7	B3[7]	Prescaler op amp mode	Power-down

Note: *For the internal temperature monitor to function, Bit 0 of Byte 2 for all 10 Quads must be set.

Features Supported on Pro I/Os

Table 2-72 lists all features supported by transmitter/receiver for single-ended and differential I/Os.

Table 2-72 • Fusion Pro I/O Features

Feature	Description
Single-ended and voltage-referenced transmitter features	• Hot insertion in every mode except PCI or 5 V input tolerant (these modes use clamp diodes and do not allow hot insertion)
	• Activation of hot insertion (disabling the clamp diode) is selectable by I/Os.
	• Weak pull-up and pull-down
	• Two slew rates
	• Skew between output buffer enable/disable time: 2 ns delay (rising edge) and 0 ns delay (falling edge); see "Selectable Skew between Output Buffer Enable/Disable Time" on page 2-149 for more information
	• Five drive strengths
	• 5 V–tolerant receiver ("5 V Input Tolerance" section on page 2-144)
	• LVTTTL/LVCMOS 3.3 V outputs compatible with 5 V TTL inputs ("5 V Output Tolerance" section on page 2-148)
	• High performance (Table 2-76 on page 2-143)
Single-ended receiver features	• Schmitt trigger option
	• ESD protection
	• Programmable delay: 0 ns if bypassed, 0.625 ns with '000' setting, 6.575 ns with '111' setting, 0.85-ns intermediate delay increments (at 25°C, 1.5 V)
	• High performance (Table 2-76 on page 2-143)
	• Separate ground planes, GND/GNDQ, for input buffers only to avoid output-induced noise in the input circuitry
Voltage-referenced differential receiver features	• Programmable Delay: 0 ns if bypassed, 0.625 ns with '000' setting, 6.575 ns with '111' setting, 0.85-ns intermediate delay increments (at 25°C, 1.5 V)
	• High performance (Table 2-76 on page 2-143)
	• Separate ground planes, GND/GNDQ, for input buffers only to avoid output-induced noise in the input circuitry
CMOS-style LVDS, BLVDS, M-LVDS, or LVPECL transmitter	• Two I/Os and external resistors are used to provide a CMOS-style LVDS, BLVDS, M-LVDS, or LVPECL transmitter solution.
	• Activation of hot insertion (disabling the clamp diode) is selectable by I/Os.
	• Weak pull-up and pull-down
	• Fast slew rate
LVDS/LVPECL differential receiver features	• ESD protection
	• High performance (Table 2-76 on page 2-143)
	• Programmable delay: 0.625 ns with '000' setting, 6.575 ns with '111' setting, 0.85-ns intermediate delay increments (at 25°C, 1.5 V)
	• Separate input buffer ground and power planes to avoid output-induced noise in the input circuitry

2.5 V LVCMOS

Low-Voltage CMOS for 2.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 2.5 V applications.

Table 2-110 • Minimum and Maximum DC Input and Output Levels

2.5 V LVCMOS Drive Strength	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
Applicable to Pro I/O Banks												
4 mA	-0.3	0.7	1.7	3.6	0.7	1.7	4	4	18	16	10	10
8 mA	-0.3	0.7	1.7	3.6	0.7	1.7	8	8	37	32	10	10
12 mA	-0.3	0.7	1.7	3.6	0.7	1.7	12	12	74	65	10	10
16 mA	-0.3	0.7	1.7	3.6	0.7	1.7	16	16	87	83	10	10
24 mA	-0.3	0.7	1.7	3.6	0.7	1.7	24	24	124	169	10	10
Applicable to Advanced I/O Banks												
2 mA	-0.3	0.7	1.7	2.7	0.7	1.7	2	2	18	16	10	10
4 mA	-0.3	0.7	1.7	2.7	0.7	1.7	4	4	18	16	10	10
6 mA	-0.3	0.7	1.7	2.7	0.7	1.7	6	6	37	32	10	10
8 mA	-0.3	0.7	1.7	2.7	0.7	1.7	8	8	37	32	10	10
12 mA	-0.3	0.7	1.7	2.7	0.7	1.7	12	12	74	65	10	10
16 mA	-0.3	0.7	1.7	2.7	0.7	1.7	16	16	87	83	10	10
24 mA	-0.3	0.7	1.7	2.7	0.7	1.7	24	24	124	169	10	10
Applicable to Standard I/O Banks												
2 mA	-0.3	0.7	1.7	3.6	0.7	1.7	2	2	18	16	10	10
4 mA	-0.3	0.7	1.7	3.6	0.7	1.7	4	4	18	16	10	10
6 mA	-0.3	0.7	1.7	3.6	0.7	1.7	6	6	37	32	10	10
8 mA	-0.3	0.7	1.7	3.6	0.7	1.7	8	8	37	32	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

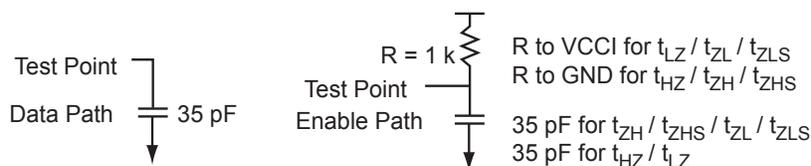


Figure 2-120 • AC Loading

Table 2-111 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	C _{LOAD} (pF)
0	2.5	1.2	–	35

Note: *Measuring point = Vtrip. See Table 2-90 on page 2-166 for a complete table of trip points.

Timing Characteristics
Table 2-128 • 1.5 V LVCMOS Low Slew

Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,
 Worst-Case $V_{CCI} = 1.4\text{ V}$
 Applicable to Pro I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.11	0.04	1.70	2.14	0.43	14.37	13.14	3.40	2.68	16.61	15.37	ns
	-1	0.56	12.00	0.04	1.44	1.82	0.36	12.22	11.17	2.90	2.28	14.13	13.08	ns
	-2	0.49	10.54	0.03	1.27	1.60	0.32	10.73	9.81	2.54	2.00	12.40	11.48	ns
4 mA	Std.	0.66	11.23	0.04	1.70	2.14	0.43	11.44	9.87	3.77	3.36	13.68	12.10	ns
	-1	0.56	9.55	0.04	1.44	1.82	0.36	9.73	8.39	3.21	2.86	11.63	10.29	ns
	-2	0.49	8.39	0.03	1.27	1.60	0.32	8.54	7.37	2.81	2.51	10.21	9.04	ns
8 mA	Std.	0.66	10.45	0.04	1.70	2.14	0.43	10.65	9.24	3.84	3.55	12.88	11.48	ns
	-1	0.56	8.89	0.04	1.44	1.82	0.36	9.06	7.86	3.27	3.02	10.96	9.76	ns
	-2	0.49	7.81	0.03	1.27	1.60	0.32	7.95	6.90	2.87	2.65	9.62	8.57	ns
12 mA	Std.	0.66	10.02	0.04	1.70	2.14	0.43	10.20	9.23	3.97	4.22	12.44	11.47	ns
	-1	0.56	8.52	0.04	1.44	1.82	0.36	8.68	7.85	3.38	3.59	10.58	9.75	ns
	-2	0.49	7.48	0.03	1.27	1.60	0.32	7.62	6.89	2.97	3.15	9.29	8.56	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7 on page 3-9](#).

Table 2-129 • 1.5 V LVCMOS High Slew

Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,
 Worst-Case $V_{CCI} = 1.4\text{ V}$
 Applicable to Pro I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	8.53	0.04	1.70	2.14	0.43	7.26	8.53	3.39	2.79	9.50	10.77	ns
	-1	0.56	7.26	0.04	1.44	1.82	0.36	6.18	7.26	2.89	2.37	8.08	9.16	ns
	-2	0.49	6.37	0.03	1.27	1.60	0.32	5.42	6.37	2.53	2.08	7.09	8.04	ns
4 mA	Std.	0.66	5.41	0.04	1.70	2.14	0.43	5.22	5.41	3.75	3.48	7.45	7.65	ns
	-1	0.56	4.60	0.04	1.44	1.82	0.36	4.44	4.60	3.19	2.96	6.34	6.50	ns
	-2	0.49	4.04	0.03	1.27	1.60	0.32	3.89	4.04	2.80	2.60	5.56	5.71	ns
8 mA	Std.	0.66	4.80	0.04	1.70	2.14	0.43	4.89	4.75	3.83	3.67	7.13	6.98	ns
	-1	0.56	4.09	0.04	1.44	1.82	0.36	4.16	4.04	3.26	3.12	6.06	5.94	ns
	-2	0.49	3.59	0.03	1.27	1.60	0.32	3.65	3.54	2.86	2.74	5.32	5.21	ns
12 mA	Std.	0.66	4.42	0.04	1.70	2.14	0.43	4.50	3.62	3.96	4.37	6.74	5.86	ns
	-1	0.56	3.76	0.04	1.44	1.82	0.36	3.83	3.08	3.37	3.72	5.73	4.98	ns
	-2	0.49	3.30	0.03	1.27	1.60	0.32	3.36	2.70	2.96	3.27	5.03	4.37	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7 on page 3-9](#).

Table 2-174 • Parameter Definitions and Measuring Nodes

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t _{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t _{OSUD}	Data Setup Time for the Output Data Register	F, H
t _{OHD}	Data Hold Time for the Output Data Register	F, H
t _{OSUE}	Enable Setup Time for the Output Data Register	G, H
t _{OHE}	Enable Hold Time for the Output Data Register	G, H
t _{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
t _{OREMPRE}	Asynchronous Preset Removal Time for the Output Data Register	L, H
t _{ORECPRE}	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t _{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t _{OESUD}	Data Setup Time for the Output Enable Register	J, H
t _{OEHD}	Data Hold Time for the Output Enable Register	J, H
t _{OESUE}	Enable Setup Time for the Output Enable Register	K, H
t _{OEHE}	Enable Hold Time for the Output Enable Register	K, H
t _{OEPRE2Q}	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
t _{OEREMPRE}	Asynchronous Preset Removal Time for the Output Enable Register	I, H
t _{OERECPRE}	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t _{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t _{ISUD}	Data Setup Time for the Input Data Register	C, A
t _{IHD}	Data Hold Time for the Input Data Register	C, A
t _{ISUE}	Enable Setup Time for the Input Data Register	B, A
t _{IHE}	Enable Hold Time for the Input Data Register	B, A
t _{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
t _{IEMPRE}	Asynchronous Preset Removal Time for the Input Data Register	D, A
t _{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-137 on page 2-212 for more information.

Pin Descriptions

Supply Pins

GND **Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ **Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ needs to always be connected on the board to GND. Note: In FG256, FG484, and FG676 packages, GNDQ and GND pins are connected within the package and are labeled as GND pins in the respective package pin assignment tables.

ADCGNDREF **Analog Reference Ground**

Analog ground reference used by the ADC. This pad should be connected to a quiet analog ground.

GND A **Ground (analog)**

Quiet ground supply voltage to the Analog Block of Fusion devices. The use of a separate analog ground helps isolate the analog functionality of the Fusion device from any digital switching noise. A 0.2 V maximum differential voltage between GND and GND A/GNDQ should apply to system implementation.

GND AQ **Ground (analog quiet)**

Quiet ground supply voltage to the analog I/O of Fusion devices. The use of a separate analog ground helps isolate the analog functionality of the Fusion device from any digital switching noise. A 0.2 V maximum differential voltage between GND and GND A/GNDQ should apply to system implementation. Note: In FG256, FG484, and FG676 packages, GND AQ and GND A pins are connected within the package and are labeled as GND A pins in the respective package pin assignment tables.

GND NVM **Flash Memory Ground**

Ground supply used by the Fusion device's flash memory block module(s).

GND OSC **Oscillator Ground**

Ground supply for both integrated RC oscillator and crystal oscillator circuit.

VCC15 A **Analog Power Supply (1.5 V)**

1.5 V clean analog power supply input for use by the 1.5 V portion of the analog circuitry.

VCC33 A **Analog Power Supply (3.3 V)**

3.3 V clean analog power supply input for use by the 3.3 V portion of the analog circuitry.

VCC33 N **Negative 3.3 V Output**

This is the -3.3 V output from the voltage converter. A 2.2 μ F capacitor must be connected from this pin to ground.

VCC33 PMP **Analog Power Supply (3.3 V)**

3.3 V clean analog power supply input for use by the analog charge pump. To avoid high current draw, VCC33 PMP should be powered up simultaneously with or after VCC33 A.

VCC NVM **Flash Memory Block Power Supply (1.5 V)**

1.5 V power supply input used by the Fusion device's flash memory block module(s). To avoid high current draw, VCC should be powered up before or simultaneously with VCC NVM.

VCC OSC **Oscillator Power Supply (3.3 V)**

Power supply for both integrated RC oscillator and crystal oscillator circuit. The internal 100 MHz oscillator, powered by the VCC OSC pin, is needed for device programming, operation of the VDDN33 pump, and eNVM operation. VCC OSC is off only when VCCA is off. VCC OSC must be powered whenever the Fusion device needs to function.

ATRTNx Temperature Monitor Return

AT returns are the returns for the temperature sensors. The cathode terminal of the external diodes should be connected to these pins. There is one analog return pin for every two Analog Quads. The x in the ATRTNx designator indicates the quad pairing (x = 0 for AQ1 and AQ2, x = 1 for AQ2 and AQ3, ..., x = 4 for AQ8 and AQ9). The signals that drive these pins are called out as ATRETURNxy in the software (where x and y refer to the quads that share the return signal). ATRTN is internally connected to ground. It can be left floating when it is unused. The maximum capacitance allowed across the AT pins is 500 pF.

GL Globals

GL I/Os have access to certain clock conditioning circuitry (and the PLL) and/or have direct access to the global network (spines). Additionally, the global I/Os can be used as Pro I/Os since they have identical capabilities. Unused GL pins are configured as inputs with pull-up resistors. See more detailed descriptions of global I/O connectivity in the "[Clock Conditioning Circuits](#)" section on page 2-22.

Refer to the "[User I/O Naming Convention](#)" section on page 2-158 for a description of naming of global pins.

JTAG Pins

Fusion devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the Fusion part must be supplied to allow JTAG signals to transition the Fusion device.

Isolating the JTAG power supply in a separate I/O bank gives greater flexibility with supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned to be used, the VJTAG pin together with the TRST pin could be tied to GND.

TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND or VJTAG through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 k Ω will satisfy the requirements. Refer to [Table 2-183](#) for more information.

Table 2-183 • Recommended Tie-Off Values for the TCK and TRST Pins

VJTAG	Tie-Off Resistance ^{2, 3}
VJTAG at 3.3 V	200 Ω to 1 k Ω
VJTAG at 2.5 V	200 Ω to 1 k Ω
VJTAG at 1.8 V	500 Ω to 1 k Ω
VJTAG at 1.5 V	500 Ω to 1 k Ω

Notes:

1. Equivalent parallel resistance if more than one device is on JTAG chain.
2. The TCK pin can be pulled up/down.
3. The TRST pin can only be pulled down.

TDI Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

TDO Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

Table 3-2 • Recommended Operating Conditions¹

Symbol	Parameter ²	Commercial	Industrial	Units	
T _J	Junction temperature	0 to +85	-40 to +100	°C	
VCC	1.5 V DC core supply voltage	1.425 to 1.575	1.425 to 1.575	V	
VJTAG	JTAG DC voltage	1.4 to 3.6	1.4 to 3.6	V	
VPUMP	Programming voltage	Programming mode ³	3.15 to 3.45	3.15 to 3.45	V
		Operation ⁴	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL)	1.425 to 1.575	1.425 to 1.575	V	
VCCI	1.5 V DC supply voltage	1.425 to 1.575	1.425 to 1.575	V	
	1.8 V DC supply voltage	1.7 to 1.9	1.7 to 1.9	V	
	2.5 V DC supply voltage	2.3 to 2.7	2.3 to 2.7	V	
	3.3 V DC supply voltage	3.0 to 3.6	3.0 to 3.6	V	
	LVDS differential I/O	2.375 to 2.625	2.375 to 2.625	V	
	LVPECL differential I/O	3.0 to 3.6	3.0 to 3.6	V	
VCC33A	+3.3 V power supply	2.97 to 3.63	2.97 to 3.63	V	
VCC33PMP	+3.3 V power supply	2.97 to 3.63	2.97 to 3.63	V	
VAREF	Voltage reference for ADC	2.527 to 2.593	2.527 to 2.593	V	
VCC15A ⁵	Digital power supply for the analog system	1.425 to 1.575	1.425 to 1.575	V	
VCCNVM	Embedded flash power supply	1.425 to 1.575	1.425 to 1.575	V	
VCCOSC	Oscillator power supply	2.97 to 3.63	2.97 to 3.63	V	
AV, AC ⁶	Unpowered, ADC reset asserted or unconfigured	-10.5 to 12.0	-10.5 to 11.6	V	
	Analog input (+16 V to +2 V prescaler range)	-0.3 to 12.0	-0.3 to 11.6	V	
	Analog input (+1 V to +0.125 V prescaler range)	-0.3 to 3.6	-0.3 to 3.6	V	
	Analog input (-16 V to -2 V prescaler range)	-10.5 to 0.3	-10.5 to 0.3	V	
	Analog input (-1 V to -0.125 V prescaler range)	-3.6 to 0.3	-3.6 to 0.3	V	
	Analog input (direct input to ADC)	-0.3 to 3.6	-0.3 to 3.6	V	
	Digital input	-0.3 to 12.0	-0.3 to 11.6	V	
AG ⁶	Unpowered, ADC reset asserted or unconfigured	-10.5 to 12.0	-10.5 to 11.6	V	
	Low Current Mode (1 μA, 3 μA, 10 μA, 30 μA)	-0.3 to 12.0	-0.3 to 11.6	V	
	Low Current Mode (-1 μA, -3 μA, -10 μA, -30 μA)	-10.5 to 0.3	-10.5 to 0.3	V	
	High Current Mode ⁷	-10.5 to 12.0	-10.5 to 11.6	V	
AT ⁶	Unpowered, ADC reset asserted or unconfigured	-0.3 to 15.5	-0.3 to 14.5	V	
	Analog input (+16 V, +4 V prescaler range)	-0.3 to 15.5	-0.3 to 14.5	V	
	Analog input (direct input to ADC)	-0.3 to 3.6	-0.3 to 3.6	V	
	Digital input	-0.3 to 15.5	-0.3 to 14.5	V	

Notes:

1. The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-85 on page 2-157.
2. All parameters representing voltages are measured with respect to GND unless otherwise specified.
3. The programming temperature range supported is $T_{ambient} = 0^{\circ}\text{C}$ to 85°C .
4. VPUMP can be left floating during normal operation (not programming mode).
5. Violating the V_{CC15A} recommended voltage supply during an embedded flash program cycle can corrupt the page being programmed.
6. The input voltage may overshoot by up to 500 mV above the Recommended Maximum (150 mV in Direct mode), provided the duration of the overshoot is less than 50% of the operating lifetime of the device.
7. The AG pad should also conform to the limits as specified in Table 2-48 on page 2-114.

Calculating Power Dissipation

Quiescent Supply Current

Table 3-8 • AFS1500 Quiescent Supply Current Characteristics

Parameter	Description	Conditions	Temp.	Min.	Typ.	Max.	Unit
ICC ¹	1.5 V quiescent current	Operational standby ⁴ , VCC = 1.575 V	T _J = 25°C		20	40	mA
			T _J = 85°C		32	65	mA
			T _J = 100°C		59	120	mA
		Standby mode ⁵ or Sleep mode ⁶ , VCC = 0 V			0	0	μA
ICC33 ²	3.3 V analog supplies current	Operational standby ⁴ , VCC33 = 3.63 V	T _J = 25°C		9.8	13	mA
			T _J = 85°C		10.7	14	mA
			T _J = 100°C		10.8	15	mA
		Operational standby, only Analog Quad and -3.3 V output ON, VCC33 = 3.63 V	T _J = 25°C		0.31	2	mA
			T _J = 85°C		0.35	2	mA
			T _J = 100°C		0.45	2	mA
		Standby mode ⁵ , VCC33 = 3.63 V	T _J = 25°C		2.9	3.6	mA
			T _J = 85°C		2.9	4	mA
			T _J = 100°C		3.3	6	mA
		Sleep mode ⁶ , VCC33 = 3.63 V	T _J = 25°C		17	19	μA
			T _J = 85°C		18	20	μA
			T _J = 100°C		24	25	μA
ICCI ³	I/O quiescent current	Operational standby ⁴ , Standby mode, and Sleep Mode ⁶ , VCC1x = 3.63 V	T _J = 25°C		417	649	μA
			T _J = 85°C		417	649	μA
			T _J = 100°C		417	649	μA

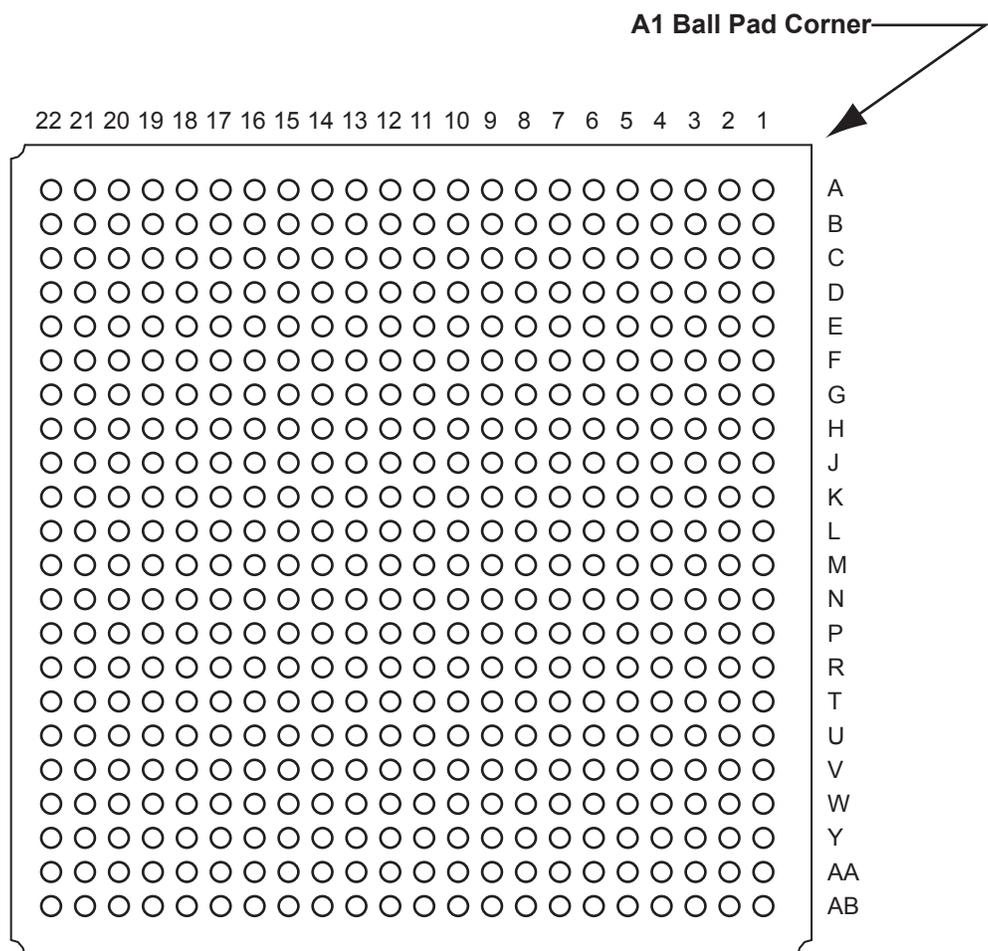
Notes:

1. ICC is the 1.5 V power supplies, ICC and ICC15A.
2. ICC33A includes ICC33A, ICC33PMP, and ICCOSC.
3. ICCI includes all ICCI0, ICCI1, ICCI2, and ICCI4.
4. Operational standby is when the Fusion device is powered up, all blocks are used, no I/O is toggling, Voltage Regulator is loaded with 200 mA, VCC33PMP is ON, XTAL is ON, and ADC is ON.
5. XTAL is configured as high gain, VCC = VJTAG = VPUMP = 0 V.
6. Sleep Mode, VCC = VJTAG = VPUMP = 0 V.

QN180		
Pin Number	AFS090 Function	AFS250 Function
A1	GNDQ	GNDQ
A2	VCCIB3	VCCIB3
A3	GAB2/IO52NDB3V0	IO74NDB3V0
A4	GFA2/IO51NDB3V0	IO71NDB3V0
A5	GFC2/IO50NDB3V0	IO69NPB3V0
A6	VCCIB3	VCCIB3
A7	GFA1/IO47PPB3V0	GFB1/IO67PPB3V0
A8	GEB0/IO45NDB3V0	NC
A9	XTAL1	XTAL1
A10	GNDOSC	GNDOSC
A11	GEC2/IO43PPB3V0	GEA1/IO61PPB3V0
A12	IO43NPB3V0	GEA0/IO61NPB3V0
A13	NC	VCCIB3
A14	GNDNVM	GNDNVM
A15	PCAP	PCAP
A16	VCC33PMP	VCC33PMP
A17	NC	NC
A18	AV0	AV0
A19	AG0	AG0
A20	ATRTN0	ATRTN0
A21	AG1	AG1
A22	AC1	AC1
A23	AV2	AV2
A24	AT2	AT2
A25	AT3	AT3
A26	AC3	AC3
A27	AV4	AV4
A28	AC4	AC4
A29	AT4	AT4
A30	NC	AG5
A31	NC	AV5
A32	ADCGNDREF	ADCGNDREF
A33	VCC33A	VCC33A
A34	GNDA	GNDA
A35	PTBASE	PTBASE
A36	VCCNVM	VCCNVM

QN180		
Pin Number	AFS090 Function	AFS250 Function
A37	VPUMP	VPUMP
A38	TDI	TDI
A39	TDO	TDO
A40	VJTAG	VJTAG
A41	GDB1/IO39PPB1V0	GDA1/IO54PPB1V0
A42	GDC1/IO38PDB1V0	GDB1/IO53PDB1V0
A43	VCC	VCC
A44	GCB0/IO35NPB1V0	GCB0/IO48NPB1V0
A45	GCC1/IO34PDB1V0	GCC1/IO47PDB1V0
A46	VCCIB1	VCCIB1
A47	GBC2/IO32PPB1V0	GGB2/IO41PPB1V0
A48	VCCIB1	VCCIB1
A49	NC	NC
A50	GBA0/IO29RSB0V0	GBB1/IO37RSB0V0
A51	VCCIB0	VCCIB0
A52	GBB0/IO27RSB0V0	GBC0/IO34RSB0V0
A53	GBC1/IO26RSB0V0	IO33RSB0V0
A54	IO24RSB0V0	IO29RSB0V0
A55	IO21RSB0V0	IO26RSB0V0
A56	VCCIB0	VCCIB0
A57	IO15RSB0V0	IO21RSB0V0
A58	IO10RSB0V0	IO13RSB0V0
A59	IO07RSB0V0	IO10RSB0V0
A60	GAC0/IO04RSB0V0	IO06RSB0V0
A61	GAB1/IO03RSB0V0	GAC1/IO05RSB0V0
A62	VCC	VCC
A63	GAA1/IO01RSB0V0	GAB0/IO02RSB0V0
A64	NC	NC
B1	VCOMPLA	VCOMPLA
B2	GAA2/IO52PDB3V0	GAC2/IO74PDB3V0
B3	GAC2/IO51PDB3V0	GFA2/IO71PDB3V0
B4	GFB2/IO50PDB3V0	GFB2/IO70PSB3V0
B5	VCC	VCC
B6	GFC0/IO49NDB3V0	GFC0/IO68NDB3V0
B7	GEB1/IO45PDB3V0	NC
B8	VCCOSC	VCCOSC

FG484



Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/default.aspx>.

Revision	Changes	Page
v2.0, Revision 1 (continued)	Table 3-6 • Package Thermal Resistance was updated to include new data.	3-7
	In EQ 4 to EQ 6, the junction temperature was changed from 110°C to 100°C.	3-8 to 3-8
	Table 3-8 • AFS1500 Quiescent Supply Current Characteristics through Table 3-11 • AFS090 Quiescent Supply Current Characteristics are new and have replaced the Quiescent Supply Current Characteristics (IDDQ) table.	3-10 to 3-16
	In Table 3-14 • Different Components Contributing to the Dynamic Power Consumption in Fusion Devices, the power supply for PAC9 and PAC10 were changed from VMV/VCC to VCCI.	3-22
	In Table 3-15 • Different Components Contributing to the Static Power Consumption in Fusion Devices, the power supply for PDC7 and PDC8 were changed from VMV/VCC to VCCI. PDC1 was updated from TBD to 18.	3-23
	The "QN108" table was updated to remove the duplicates of pins B12 and B34.	4-2
Preliminary v1.7 (October 2008)	The version number category was changed from Advance to Preliminary, which means the datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.	
	For the VIL and VIH parameters, 0.30 * VCCI was changed to 0.35 * VCCI and 0.70 * VCCI was changed to 0.65 * VCCI in Table 2-126 • Minimum and Maximum DC Input and Output Levels.	2-193
	The version number category was changed from Advance to Preliminary, which means the datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.	N/A
	The following updates were made to Table 2-141 • Minimum and Maximum DC Input and Output Levels: Temperature Digital Output 213 00 1111 1101 283 01 0001 1011 358 01 0110 0110 – only the digital output was updated. Temperature 358 remains in the temperature column.	2-200
	In Advance v1.2, the "VAREF Analog Reference Voltage" pin description was significantly updated but the change was not noted in the change table.	2-225
Advance v1.6 (August 2008)	The title of the datasheet changed from Actel Programmable System Chips to Actel Fusion Mixed Signal FPGAs. In addition, all instances of programmable system chip were changed to mixed signal FPGA.	N/A
	The references to the <i>Peripherals User's Guide</i> in the "No-Glitch MUX (NGMUX)" section and "Voltage Regulator Power Supply Monitor (VRPSM)" section were changed to <i>Fusion Handbook</i> .	2-32, 2-42
Advance v1.5 (July 2008)	The following bullet was updated from High-Voltage Input Tolerance: ±12 V to High-Voltage Input Tolerance: 10.5 V to 12 V.	I
	The following bullet was updated from Programmable 1, 3, 10, 30 µA and 25 mA Drive Strengths to Programmable 1, 3, 10, 30 µA and 20 mA Drive Strengths.	I